

# Amin Rassekh

## List of Publications by Year in descending order

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Version: 2024-02-01

8  
papers

97  
citations

1684188  
5  
h-index

1588992  
8  
g-index

8  
all docs

8  
docs citations

8  
times ranked

81  
citing authors

| # | ARTICLE   | IF  | CITATIONS |
|---|---|-----|-----------|
| 1 | Nonhysteretic Condition in Negative Capacitance Junctionless FETs. IEEE Transactions on Electron Devices, 2022, 69, 820-826.  | 3.0 | 10        |
| 2 | Design Space of Negative Capacitance in FETs. IEEE Nanotechnology Magazine, 2022, 21, 236-243.  | 2.0 | 6         |
| 3 | Tunneling Current Through a Double Quantum Dots System. IEEE Access, 2022, 10, 75245-75256.   | 4.2 | 2         |
| 4 | Negative Capacitance Double-Gate Junctionless FETs: A Charge-Based Modeling Investigation of Swing, Overdrive and Short Channel Effect. IEEE Journal of the Electron Devices Society, 2020, 8, 939-947. | 2.1 | 31        |
| 5 | A single-gate SOI nanosheet junctionless transistor at 10-nm gate length: design guidelines and comparison with the conventional SOI FinFET. Journal of Computational Electronics, 2020, 19, 631-639.   | 2.5 | 20        |
| 6 | An Experimental Study on Mixed-Dimensional 1D-2D van der Waals Single-Walled Carbon Nanotube-WSe <sub>2</sub> Hetero-Junction. IEEE Electron Device Letters, 2020, 41, 645-648.                         | 3.9 | 10        |
| 7 | Communication at the Speed of Light (CaSoL): A New Paradigm for Designing Global Wires. IEEE Transactions on Electron Devices, 2019, 66, 3466-3472.   | 3.0 | 1         |
| 8 | Modeling Interface Charge Traps in Junctionless FETs, Including Temperature Effects. IEEE Transactions on Electron Devices, 2019, 66, 4653-4659.  | 3.0 | 17        |